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XHB06

Schottky Barrier Diode

200mA 40V Low Leak(0.37mm)

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Chip Information

Chip Size	0.37 x 0.37mm
Pad Size	0.30 x 0.30mm
Chip Quantity	80698 pcs/wafer
Scribe Line Width	40um
Passivation	SIN
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	40	V	
Average Forward Rectified Current	IF(AV)	200	mA	
Peak Forward Surge Current	IFSM	1	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition	
Maximum Forward Voltage	VF1	0.600	0.575	0.530	V	IF=200mA	Ta=25degC
	VF2	0.450	0.425	0.332	V	IF=10mA	Ta=25degC
	VF3				V		
	VF4				V		
	VF5				V		
Maximum DC Reverse Current	IR1	1	0.3	0.08	uA	VR=10V	Ta=25degC
	IR2	2	1	0.35	uA	VR=40V	Ta=25degC
	IR3				uA		
	IR4				uA		
Reverse Breakdown Voltage	BV	40	44	52	V	IR=10uA	
Junction Capacitance	Cj				pF		
Reverse Recovery Time	trr				nS		

Ordering Information

Chip Type	Chip Thickness	Back Metal
XHB06B	140 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)
XHB06C	140 +/- 20um	Au(For Eutectic)
XHB06Y	120 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:
Designed For RB520S-30,RB520S-40